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Datasheet of PMEG2002ESF,315 - DIODE SCHOTTKY 20V 200MA 2DSN Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection in a DSN0603-2 (SOD962-2) leadless ultra small Surface-Mounted Device (SMD) package.

2. Features and benefits

- Average forward current I_{F(AV)} ≤ 0.2 A
- Reverse voltage V_R ≤ 20 V
- Low forward voltage typ. V_F 310 mV
- Low reverse current typ. I_R 0.88 μA
- Ultra small and leadless SMD package
- Package height typ. 0.3 mm

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Low power consumption applications
- Ultra high-speed switching
- LED backlight for mobile application

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 125 °C; square wave		-	-	0.2	Α
		δ = 0.5 ; f = 20 kHz; $T_{amb} \le$ 115 °C; square wave	[1]	-	-	0.2	Α
V _R	reverse voltage	T _j = 25 °C		-	-	20	V
V _F	forward voltage	I_F = 10 mA; pulsed; $t_p \le 300 \text{ μs}$; $\delta \le 0.02$; T_j = 25 °C		-	310	380	mV
I _R	reverse current	$V_R = 10 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	0.37	-	μΑ

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.







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Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]		1][-] 2
2	Α	anode		sym001
			Transparent top view	
			DSN0603-2 (SOD962-2)	

^[1] The marking bar indicates the cathode.

Ordering information

Table 3. **Ordering information**

Type number	Package	ackage				
	Name	Description	Version			
PMEG2002ESF	DSN0603-2	Leadless ultra small package; 2 terminals; body $0.6 \times 0.3 \times 0.3$ mm	SOD962-2			

Marking 7.

Marking codes Table 4.

Type number	Marking code
PMEG2002ESF	E

8. **Limiting values**

Limiting values Table 5.

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	T _j = 25 °C		-	20	V
I _F	forward current	T _{sp} ≤ 120 °C		-	0.28	Α
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 125 °C; square wave		-	0.2	Α
		δ = 0.5 ; f = 20 kHz; $T_{amb} \le$ 115 °C; square wave	[1]	-	0.2	А
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ ms}; \ \delta \le 0.25$		-	1	Α
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	4.5	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	325	mW

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Symbol	Parameter	Conditions		Min	Max	Unit
			<u>[3]</u>	-	525	mW
			[1]	-	950	mW
Tj	junction temperature			-	125	°C
T _{amb}	ambient temperature			-55	125	°C
T _{stg}	storage temperature			-65	150	°C

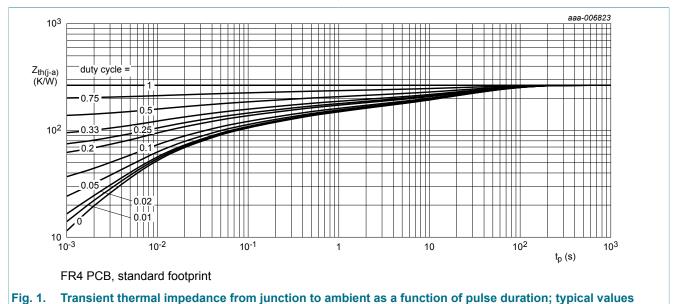
- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm² each.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistar from junction to ambient	thermal resistance		[1][2]	-	-	310	K/W
			[1][3]	-	-	190	K/W
	ambient		[1][4]	-	-	105	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	40	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm² each.
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.



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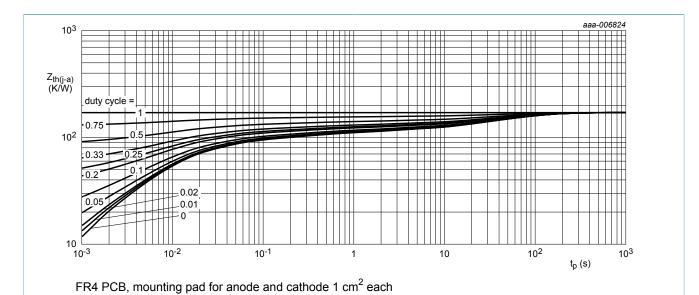


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

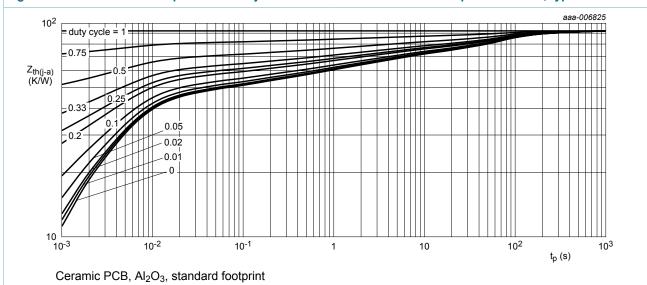


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



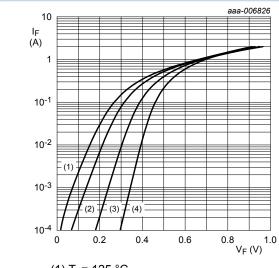
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20 V, 0.2 A low VF MEGA Schottky barrier rectifier

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F forward volt	forward voltage	I_F = 0.1 mA; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02 ; T_j = 25 °C	-	185	250	mV
		I_F = 1 mA; pulsed; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C	-	245	320	mV
		I_F = 10 mA; pulsed; $t_p \le 300 \ \mu s$; $δ \le 0.02$; T_j = 25 °C	-	310	380	mV
		I_F = 100 mA; pulsed; t_p ≤ 300 μs; $δ$ ≤ 0.02 ; T_j = 25 °C	-	390	450	mV
		I_F = 200 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_j = 25 °C	-	435	490	mV
I _R	reverse current	V _R = 6 V; T _j = 25 °C	-	0.26	1.5	μA
		V _R = 10 V; T _j = 25 °C	-	0.37	-	μA
		V _R = 20 V; T _j = 25 °C	-	0.88	3.5	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	25	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	9	-	pF
t _{rr}	reverse recovery time	I_F = 200 mA; I_R = 200 mA; $I_{R(meas)}$ = 40 mA; T_j = 25 °C	-	1.9	-	ns



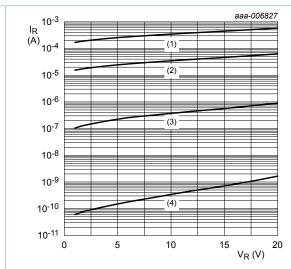


(2)
$$T_i = 85 \, ^{\circ}C$$

(3)
$$T_i = 25 \, ^{\circ}C$$

(4)
$$T_j = -40 \, ^{\circ}\text{C}$$

Fig. 4. Forward current as a function of forward voltage; typical values



- (1) $T_j = 125 \,^{\circ}\text{C}$
- (2) $T_i = 85 \,^{\circ}C$
- (3) $T_i = 25 \, ^{\circ}C$
- (4) $T_i = -40 \, ^{\circ}C$

Fig. 5. Reverse current as a function of reverse voltage; typical values

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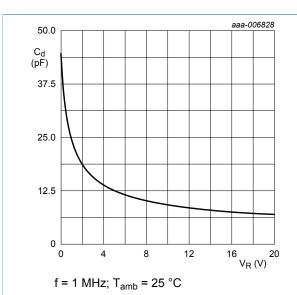
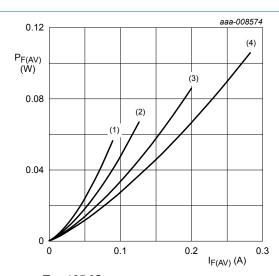


Fig. 6. Diode capacitance as a function of reverse voltage; typical values

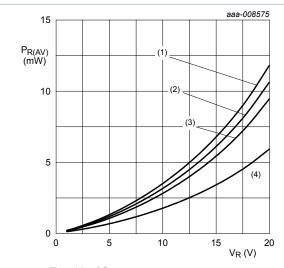


 $T_j = 125 \,^{\circ}\text{C}$ (1) $\delta = 0.1$ (2) $\delta = 0.2$

 $(3) \delta = 0.5$

 $(4) \delta = 1$

Fig. 7. Average forward power dissipation as a function of average forward current; typical values



T_j = 125 °C

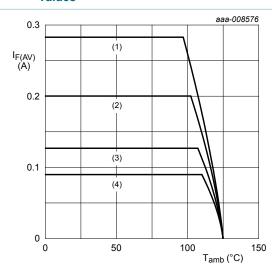
(1) $\delta = 1$ (DC)

(2) $\delta = 0.9$; f = 20 kHz

(3) $\delta = 0.8$; f = 20 kHz

(4) δ = 0.5; f = 20 kHz

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T_i = 125 °C

 $(1) \delta = 1$

 $(2) \delta = 0.5$

 $(3) \delta = 0.2$

 $(4) \delta = 0.1$

Fig. 9. Average forward current as a function of ambient temperature; typical values

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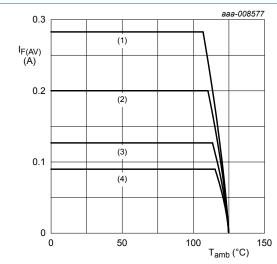
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FR4 PCB, mounting pad for anode and cathode 1

cm² each

T_i = 125 °C

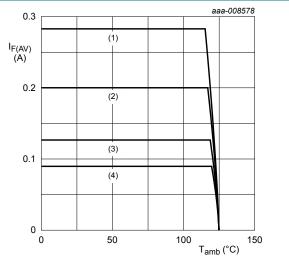
 $(1) \delta = 1$

 $(2) \delta = 0.5$

 $(3) \delta = 0.2$

 $(4) \delta = 0.1$

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

T_i = 125 °C

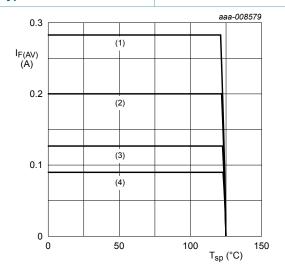
 $(1) \delta = 1$

 $(2) \delta = 0.5$

 $(3) \delta = 0.2$

 $(4) \delta = 0.1$

Fig. 11. Average forward current as a function of ambient temperature; typical values



T_i = 125 °C

 $(1) \delta = 1$

 $(2) \delta = 0.5$

 $(3) \delta = 0.2$

 $(4) \delta = 0.1$

Fig. 12. Average forward current as a function of solder point temperature; typical values

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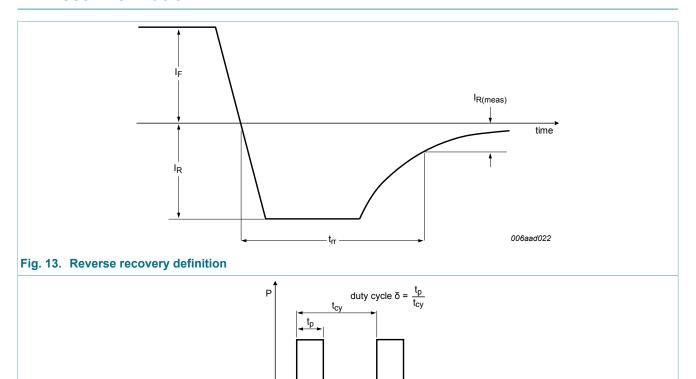


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11. Test information

Fig. 14. Duty cycle definition



The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

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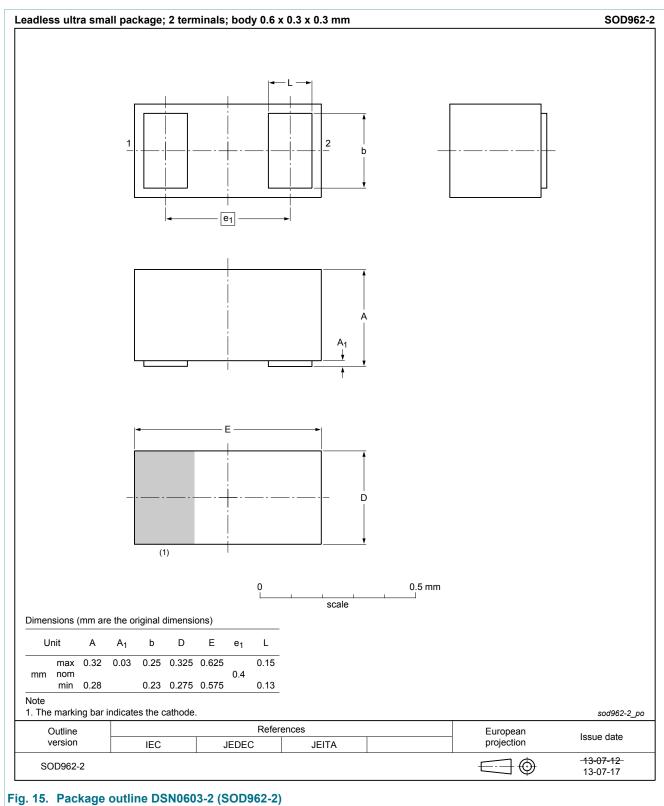


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12. Package outline

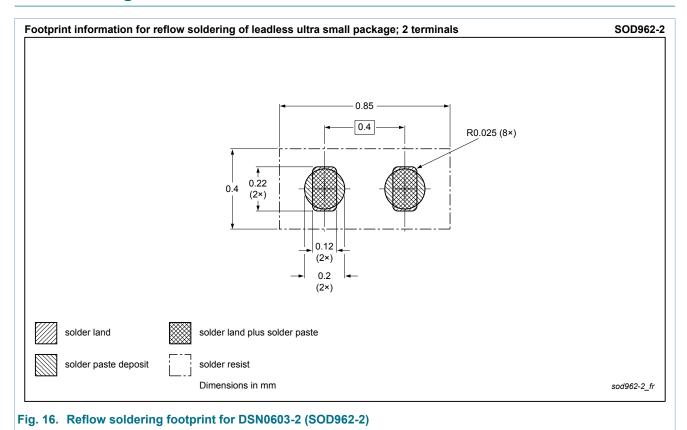




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13. Soldering



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG2002ESF v.2	20131008	Product data sheet	-	PMEG2002ESF v.1
Modifications:	 Product status char 	iged		
PMEG2002ESF v.1	20130301	Objective data sheet	-	-

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